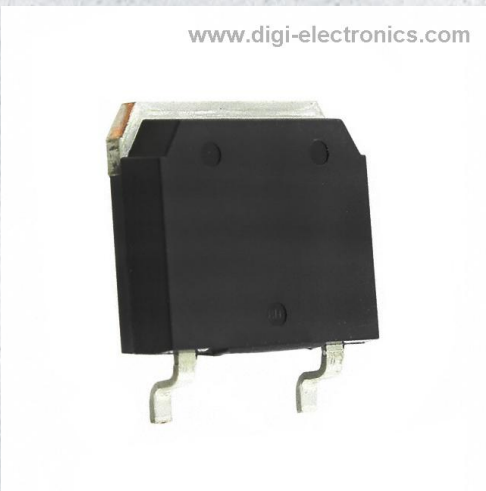
IXFT52N30Q Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	IXFT52N30Q-DG
Manufacturer	IXYS
Manufacturer Product Number	IXFT52N30Q
Description	MOSFET N-CH 300V 52A TO268
Detailed Description	N-Channel 300 V 52A (Tc) 360W (Tc) Surface Mount TO-268AA

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
IXFT52N30Q	IXYS
Series:	Product Status:
HiPerFET™	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
300 V	52A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	60mOhm @ 500mA, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 4mA	150 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	5300 pF @ 25 V
FET Feature:	Power Dissipation (Max):
-	360W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-268AA	TO-268-3, D³Pak (2 Leads + Tab), TO-268AA
Base Product Number:	
IXFT52	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	ECCN:
1 (Unlimited)	EAR99
HTSUS:	
8541.29.0095	

IXYS

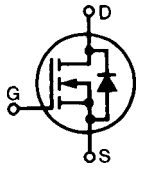
HiPerFET™ Power MOSFETs Q-Class

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}
Low Gate Charge and Capacitances

Preliminary data

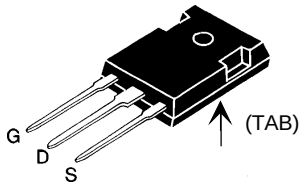
IXFH 52N30Q
IXFK 52N30Q
IXFT 52N30Q

V_{DSS} = 300 V
I_{D25} = 52 A
$R_{DS(on)}$ = 60 mΩ
t_{rr} ≤ 250 ns

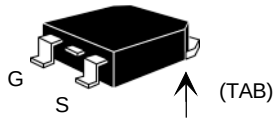


Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		300	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ		300	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C, Chip capability		52	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}		208	A
I_{AR}	T_C = 25°C		52	A
E_{AR}	T_C = 25°C		30	mJ
E_{AS}	T_C = 25°C		1.5	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/μs, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		360	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6 mm (0.063 in) from case for 10 s		300	°C
M_d	Mounting torque	TO-247	1.13/10	Nm/lb.in.
		TO-264	0.9/6	Nm/lb.in.
Weight		TO-247	6	g
		TO-264	10	g
		TO-268	4	g

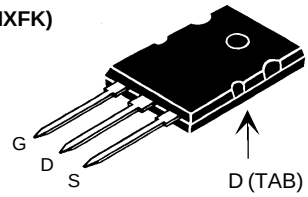
TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



TO-264 AA (IXFK)



G = Gate
S = Source
TAB = Drain

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 1 mA		300			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA		2		4	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0				±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$	T_J = 25°C			50	μA
	V_{GS} = 0 V	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5 \bullet I_{D25}$ Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %				60	mΩ

Features

- Low gate charge
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy to mount
- Space savings
- High power density

IXYS reserves the right to change limits, test conditions, and dimensions.

98522B (7/00)

IXYS

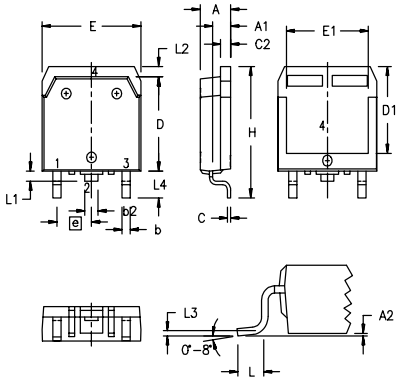
IXFH 52N30Q IXFK 52N30Q
IXFT 52N30Q

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 • I_{D25}, pulse test	22	35		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		5300		pF
C_{oss}			1010		pF
C_{rss}			200		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25} R_G = 1.5 Ω (External),		27		ns
t_r			60		ns
$t_{d(off)}$			80		ns
t_f			25		ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		150		nC
Q_{gs}			34		nC
Q_{gd}			75		nC
R_{thJC}				0.35	K/W
R_{thCK}	TO-247		0.25		K/W
	TO-264		0.15		K/W

Source-Drain Diode

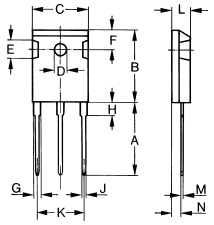
Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
I_S	V_{GS} = 0 V			52	A
I_{SM}	Repetitive; pulse width limited by T_{JM}			208	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.5	V
t_{rr}	I_F = I_S -di/dt = 100 A/µs, V_R = 100 V			250	ns
Q_{RM}			1		µC
I_{RM}			8		A

TO-268AA (D³ PAK)



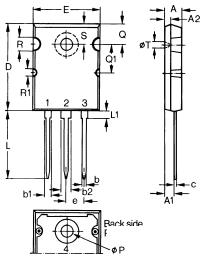
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.9	5.1	.193	.201
A_1	2.7	2.9	.106	.114
A_2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b_2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E_1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

TO-247 AD (IXFH) Outline



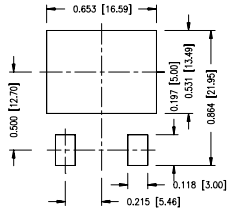
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-264 AA Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Min. Recommended Footprint



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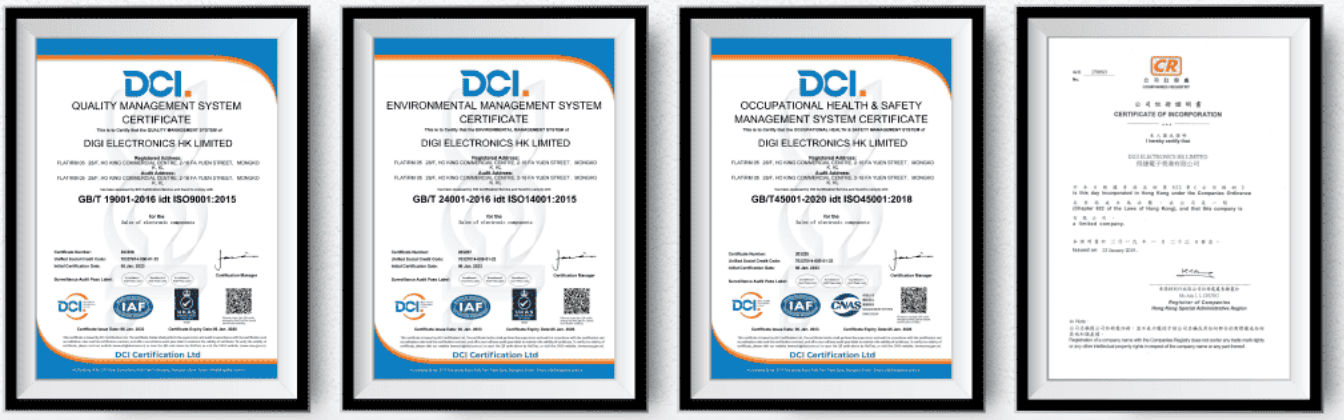

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